

## POWER SCHOTTKY RECTIFIER

**Table 1: Main Product Characteristics**

|                   |        |
|-------------------|--------|
| $I_{F(AV)}$       | 2 A    |
| $V_{RRM}$         | 60 V   |
| $T_j(\text{max})$ | 150°C  |
| $V_F(\text{max})$ | 0.55 V |

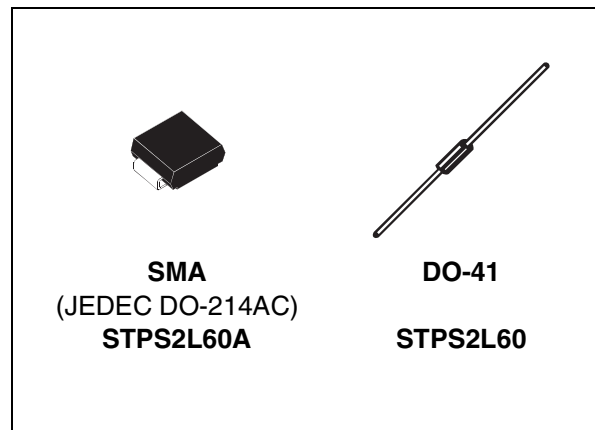
### FEATURES AND BENEFITS

- Negligible switching losses
- Low forward voltage drop
- Surface mount miniature package
- Avalanche capability specified

### DESCRIPTION

Axial and Surface Mount Power Schottky rectifiers suited to Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in SMA and DO-41, this device is especially intended for use in low voltage, high frequency inverters and small battery chargers.



**Table 2: Order Codes**

| Part Number | Marking  |
|-------------|----------|
| STPS2L60A   | S26      |
| STPS2L60    | STPS2L60 |
| STPS2L60RL  | STPS2L60 |

**Table 3: Absolute Ratings** (limiting values)

| Symbol       | Parameter                                |       | Value        | Unit |
|--------------|--|-------|--------------|------|
| $V_{RRM}$    | Repetitive peak reverse voltage          |       | 60           | V    |
| $I_{F(RMS)}$ | RMS forward current                      |       | 10           | A    |
| $I_{F(AV)}$  | Average forward current                  | SMA   | 2            | A    |
|              |  | DO-41 |              |      |
| $I_{FSM}$    | Surge non repetitive forward current     |       | 75           | A    |
| $P_{ARM}$    | Repetitive peak avalanche power          |       | 1600         | W    |
| $T_{stg}$    | Storage temperature range                |       | -65 to + 150 | °C   |
| $T_j$        | Maximum operating junction temperature * |       | 150          | °C   |
| dV/dt        | Critical rate of rise of reverse voltage |       | 10000        | V/μs |

\* :  $\frac{dP_{tot}}{dT_j} > \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

# STPS2L60

**Table 4: Thermal Resistance**

| Symbol        | Parameter        |                              | Value | Unit |
|---------------|------------------|------------------------------|-------|------|
| $R_{th(j-l)}$ | Junction to lead | SMA                          | 25    | °C/W |
|               |                  | Lead length = 10 mm<br>DO-41 | 30    |      |

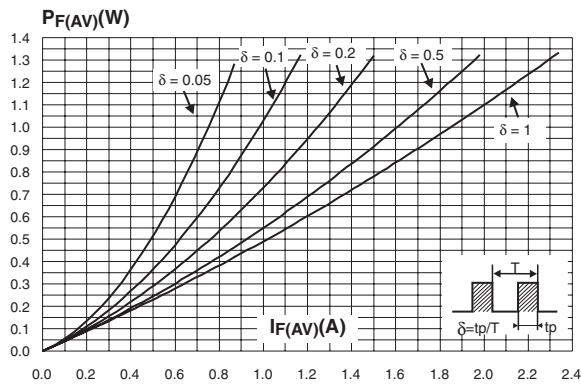
**Table 5: Static Electrical Characteristics**

| Symbol     | Parameter               | Tests conditions          |                   | Min. | Typ  | Max. | Unit          |
|------------|-------------------------|---------------------------|-------------------|------|------|------|---------------|
| $I_R^*$    | Reverse leakage current | $T_j = 25^\circ\text{C}$  | $V_R = V_{RRM}$   |      |      | 100  | $\mu\text{A}$ |
|            |                         | $T_j = 100^\circ\text{C}$ |                   |      | 2    | 10   | mA            |
| $V_F^{**}$ | Forward voltage drop    | $T_j = 25^\circ\text{C}$  | $I_F = 2\text{A}$ |      |      | 0.60 | V             |
|            |                         | $T_j = 125^\circ\text{C}$ |                   |      | 0.51 | 0.55 |               |
|            |                         | $T_j = 25^\circ\text{C}$  | $I_F = 4\text{A}$ |      |      | 0.77 |               |
|            |                         | $T_j = 125^\circ\text{C}$ |                   |      | 0.62 | 0.67 |               |

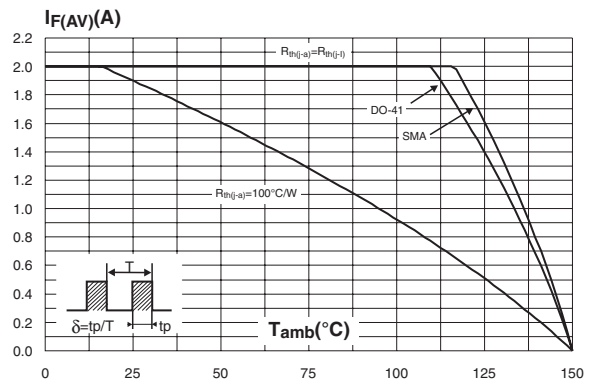
Pulse test: \*  $t_p = 380 \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:  $P = 0.43 \times I_{F(AV)} + 0.06 I_{F(RMS)}^2$

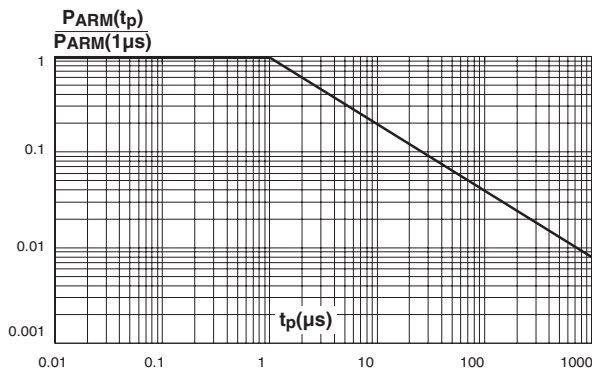
**Figure 1: Average forward power dissipation versus average forward current**



**Figure 2: Average forward current versus ambient temperature ( $\delta = 0.5$ )**



**Figure 3: Normalized avalanche power derating versus pulse duration**



**Figure 4: Normalized avalanche power derating versus junction temperature**

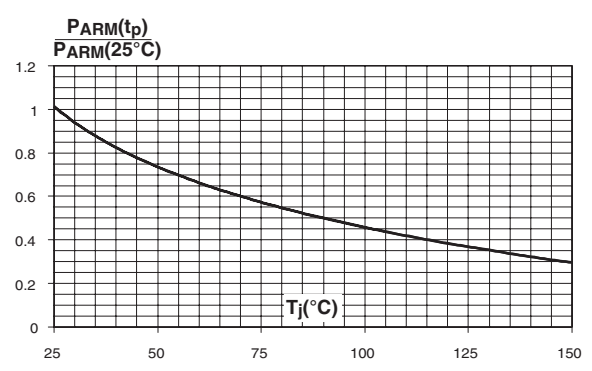


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values) (SMA)

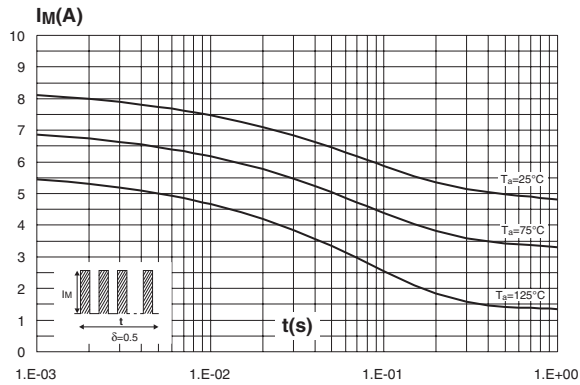


Figure 6: Non repetitive surge peak forward current versus overload duration (maximum values) (DO-41)

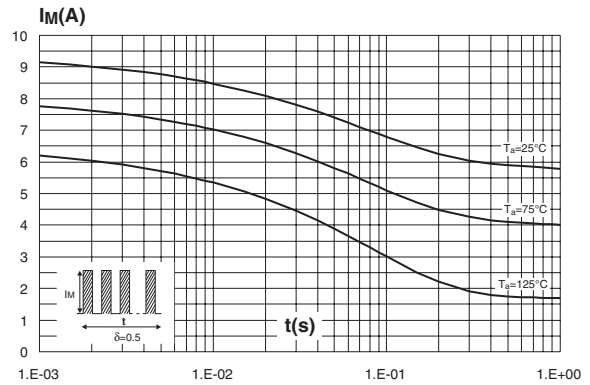


Figure 7: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, e(Cu)=35µm, recommended pad layout) (SMA)

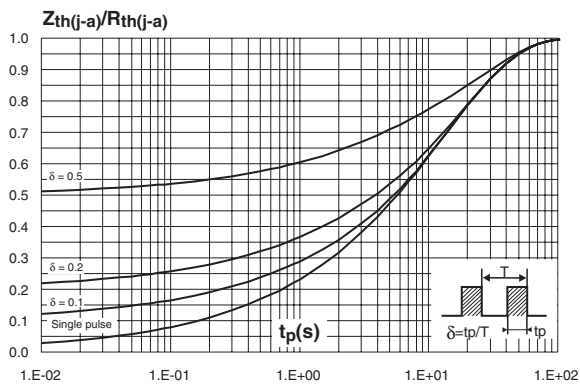


Figure 8: Relative variation of thermal impedance junction to ambient versus pulse duration (DO-41)

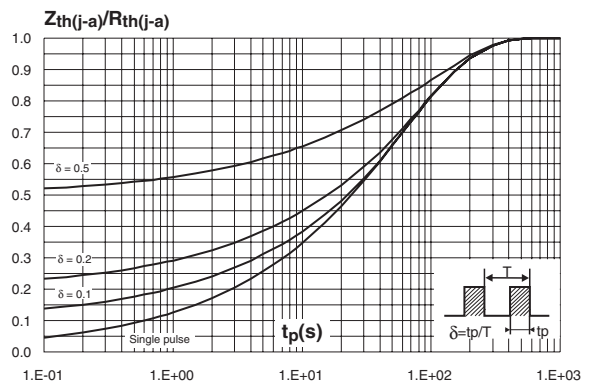


Figure 9: Reverse leakage current versus reverse voltage applied (typical values)

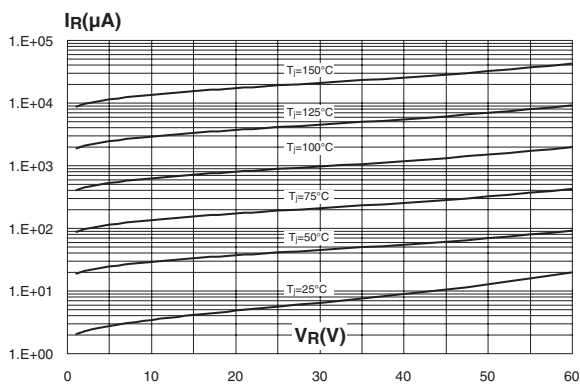


Figure 10: Junction capacitance versus reverse voltage applied (typical values)

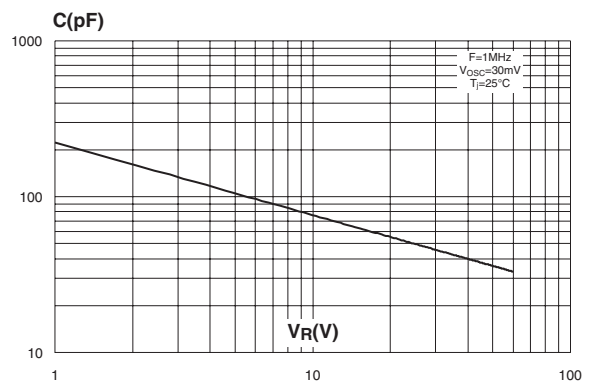


Figure 11: Forward voltage drop versus forward current (maximum values, low level)

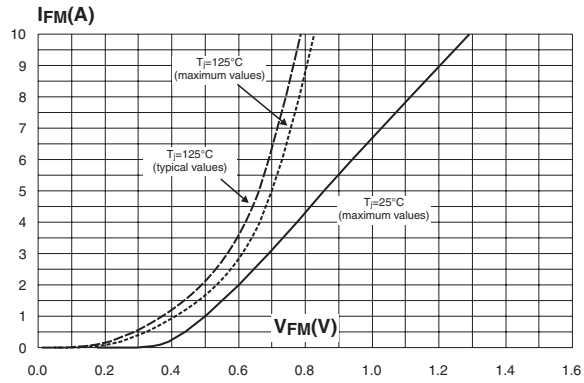


Figure 12: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35µm) (SMA)

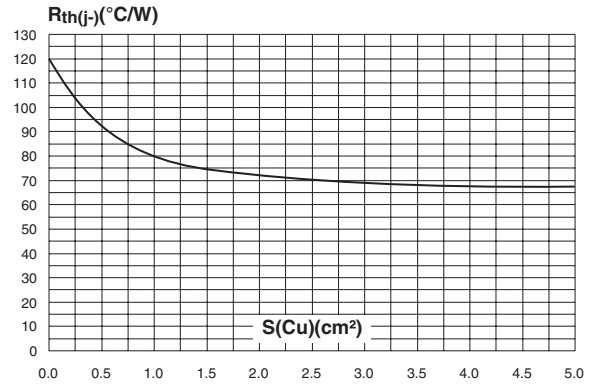


Figure 13: Thermal resistance versus lead length (DO-41)

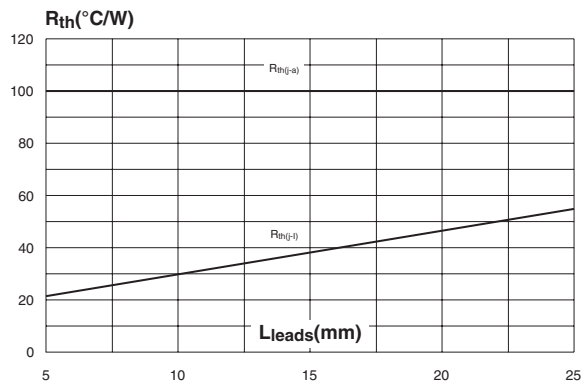
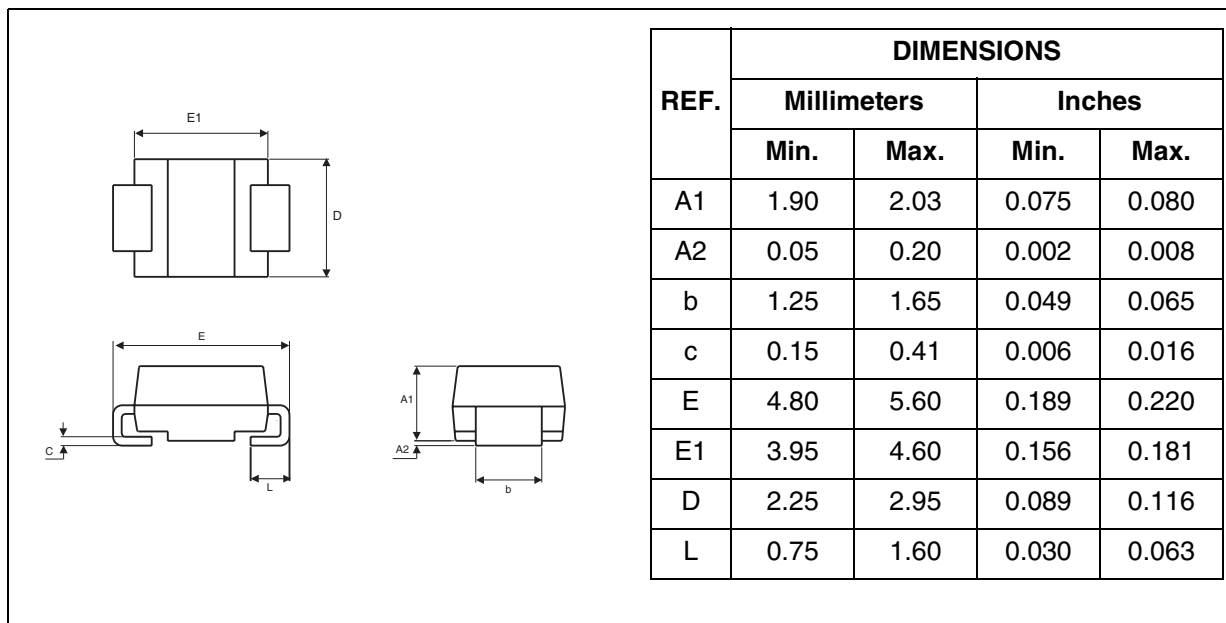
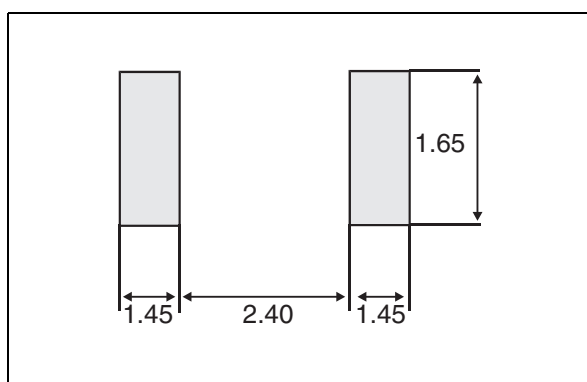


Figure 14: SMA Package Mechanical Data

Figure 15: SMA Foot Print Dimensions  
(in millimeters)

## STPS2L60

Figure 16: DO-41 Package Mechanical Data

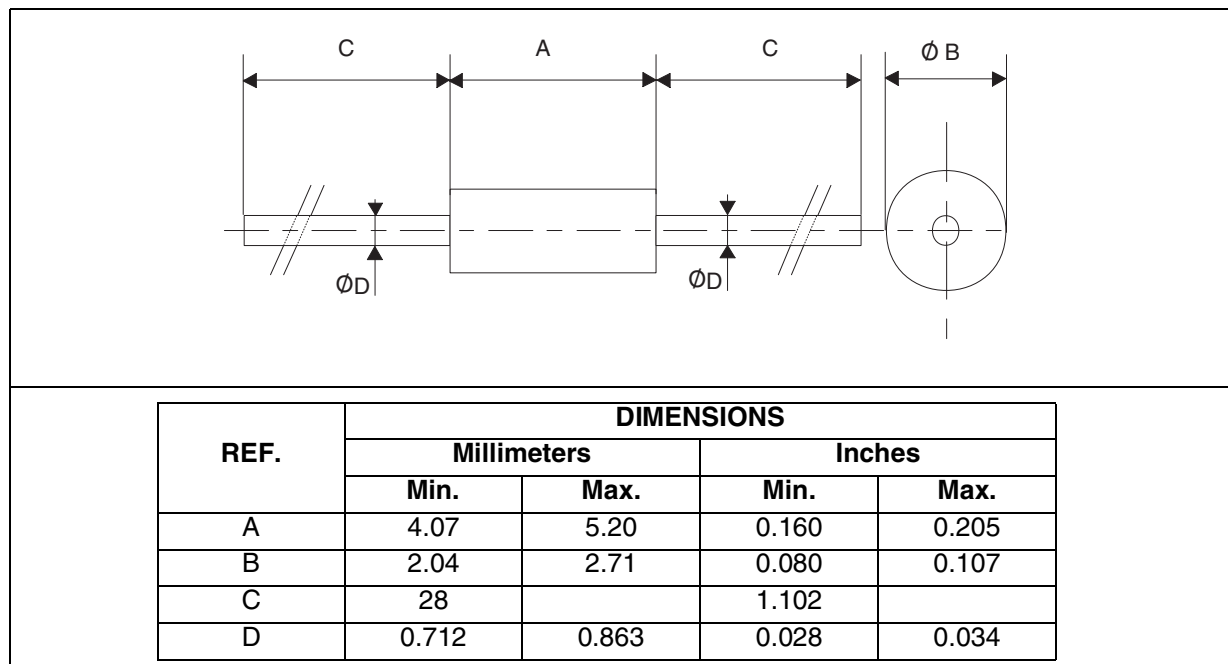


Table 6: Ordering Information

| Ordering type | Marking  | Package | Weight  | Base qty | Delivery mode |
|---------------|----------|---------|---------|----------|---------------|
| STPS2L60A     | S26      | SMA     | 0.068 g | 5000     | Tape & reel   |
| STPS2L60      | STPS2L60 | DO-41   | 0.34 g  | 2000     | Ammopack      |
| STPS2L60RL    | STPS2L60 | DO-41   | 0.34 g  | 5000     | Tape & reel   |

- Band indicates cathode
- Epoxy meets UL94, V0

Table 7: Revision History

| Date     | Revision | Description of Changes  |
|----------|----------|---|
| Jul-2003 | 2A       | Last update.  |
| Aug-2004 | 3        | SMA package dimensions update. Reference A1 max. changed from 2.70mm (0.106inc.) to 2.03mm (0.080). |

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